

## **AMENDMENTS TO THE CLAIMS**

Please replace the pending claims with the following claim listing:

1-49. **(Canceled)**

50. **(Currently Amended)** A nitride semiconductor structure comprising on a substrate:  
an n-type collector layer;  
a p-type base layer formed over said n-type collector layer, wherein said p-type base layer is p-type InGaN;  
an n-type emitter layer formed directly on a first portion of a top surface of said p-type base layer;  
an indium-containing p-type nitride semiconductor layer formed directly on a second portion of said top surface of said p-type base layer so as to contact a top surface of said p-type base layer, wherein said n-type emitter layer is not formed on the second portion, and said indium-containing p-type nitride semiconductor layer has an indium mole fraction that is higher than an indium mole fraction of said p-type InGaN base layer, and does not contact said n-type emitter layer; and  
a base electrode formed over said indium-containing p-type nitride semiconductor layer.

51. **(Previously Presented)** The nitride semiconductor structure according to claim 50, wherein said indium-containing p-type nitride semiconductor layer is p-type InGaN.

52. **(Canceled)**

53. **(Original)** The nitride semiconductor structure according to claim 51, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

54-55. **(Canceled)**

56. **(Currently Amended)** The nitride semiconductor structure according to claim [[55]] 50, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

57-76. **(Canceled)**

77. **(Previously Presented)** The nitride semiconductor structure according to claim 50, further comprising a graded layer between said p-type base layer and said n-type collector layer, wherein said graded layer has an indium mole fraction that varies gradually.

78. **(Previously Presented)** The nitride semiconductor structure according to claim 51, further comprising a graded layer between said p-type base layer and said n-type collector layer, wherein said graded layer has an indium mole fraction that varies gradually.

79. **(Canceled)**

80. **(Previously Presented)** The nitride semiconductor structure according to claim 50, wherein the base electrode is formed directly on said indium-containing p-type nitride semiconductor layer.

81. **(Currently Amended)** A nitride semiconductor structure comprising:  
an n-type collector layer;  
a p-type base layer formed over said n-type collector layer, wherein ~~[[the]]~~ said p-type base layer ~~has an etched top surface and~~ is p-type InGaN;  
an n-type emitter layer formed directly on a first portion of a top surface of said p-type base layer;  
an indium-containing p-type nitride semiconductor layer formed directly on ~~the etched~~ a second portion of said top surface of the p-type base layer which has been exposed by dry etching, wherein said indium-containing p-type nitride semiconductor layer has an indium mole fraction that is higher than an indium mole fraction of said p-type InGaN base layer, and does not contact said n-type emitter layer; and  
a base electrode formed over said indium-containing p-type nitride semiconductor layer.

82. **(Previously Presented)** The nitride semiconductor structure according to claim 81, wherein said indium-containing p-type nitride semiconductor layer comprises p-type InGaN.

83-84. **(Canceled)**

85. **(Previously Presented)** The nitride semiconductor structure according to claim 81, further comprising a graded layer between said p-type base layer and said n-type collector layer.

86. **(Previously Presented)** The nitride semiconductor structure according to claim 50, wherein said indium-containing p-type nitride semiconductor layer has a thickness of between 1 and 1000 nm.

87. **(Previously Presented)** The nitride semiconductor structure according to claim 50, wherein said indium-containing p-type nitride semiconductor layer has a thickness of about 100 nm.

88. **(Previously Presented)** The nitride semiconductor structure according to claim 81, wherein said indium-containing p-type nitride semiconductor layer has a thickness of between 1 and 1000 nm.

89. **(Previously Presented)** The nitride semiconductor structure according to claim 81, wherein said indium-containing p-type nitride semiconductor layer has a thickness of about 100 nm.

90-95. **(Canceled)**

96. **(Currently Amended)** The nitride semiconductor structure according to claim [[90]] 81, wherein the base electrode is formed directly on said indium-containing p-type nitride semiconductor layer.

97-98. **(Canceled)**